

FS30KMJ-3

High-Speed Switching Use
Nch Power MOS FET

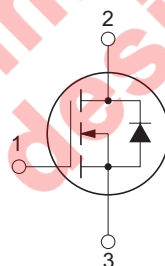
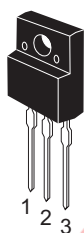
REJ03G1415-0200
(Previous: MEJ02G0080-0101)
Rev.2.00
Aug 07, 2006

Features

- Drive voltage : 4 V
- V_{DSS} : 150 V
- $r_{DS(ON) (max)}$: 86 m Ω
- I_D : 30 A
- Integrated Fast Recovery Diode (TYP.) : 100 ns
- Viso : 2000 V

Outline

RENESAS Package code: PRSS0003AB-A
(Package name: TO-220FN)



1. Gate
2. Drain
3. Source

Applications

Motor control, Lamp control, Solenoid control, DC-DC converters, etc.

Maximum Ratings

(T_c = 25°C)

Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V_{DSS}	150	V	$V_{GS} = 0$ V
Gate-source voltage	V_{GSS}	± 20	V	$V_{DS} = 0$ V
Drain current	I_D	30	A	
Drain current (Pulsed)	I_{DM}	120	A	
Avalanche drain current (Pulsed)	I_{DA}	30	A	L = 100 μ H
Source current	I_S	30	A	
Source current (Pulsed)	I_{SM}	120	A	
Maximum power dissipation	P_D	30	W	
Channel temperature	T _{ch}	- 55 to +150	°C	
Storage temperature	T _{stg}	- 55 to +150	°C	
Isolation voltage	Viso	2000	V	AC for 1 minute, Terminal to case
Mass	—	2.0	g	Typical value

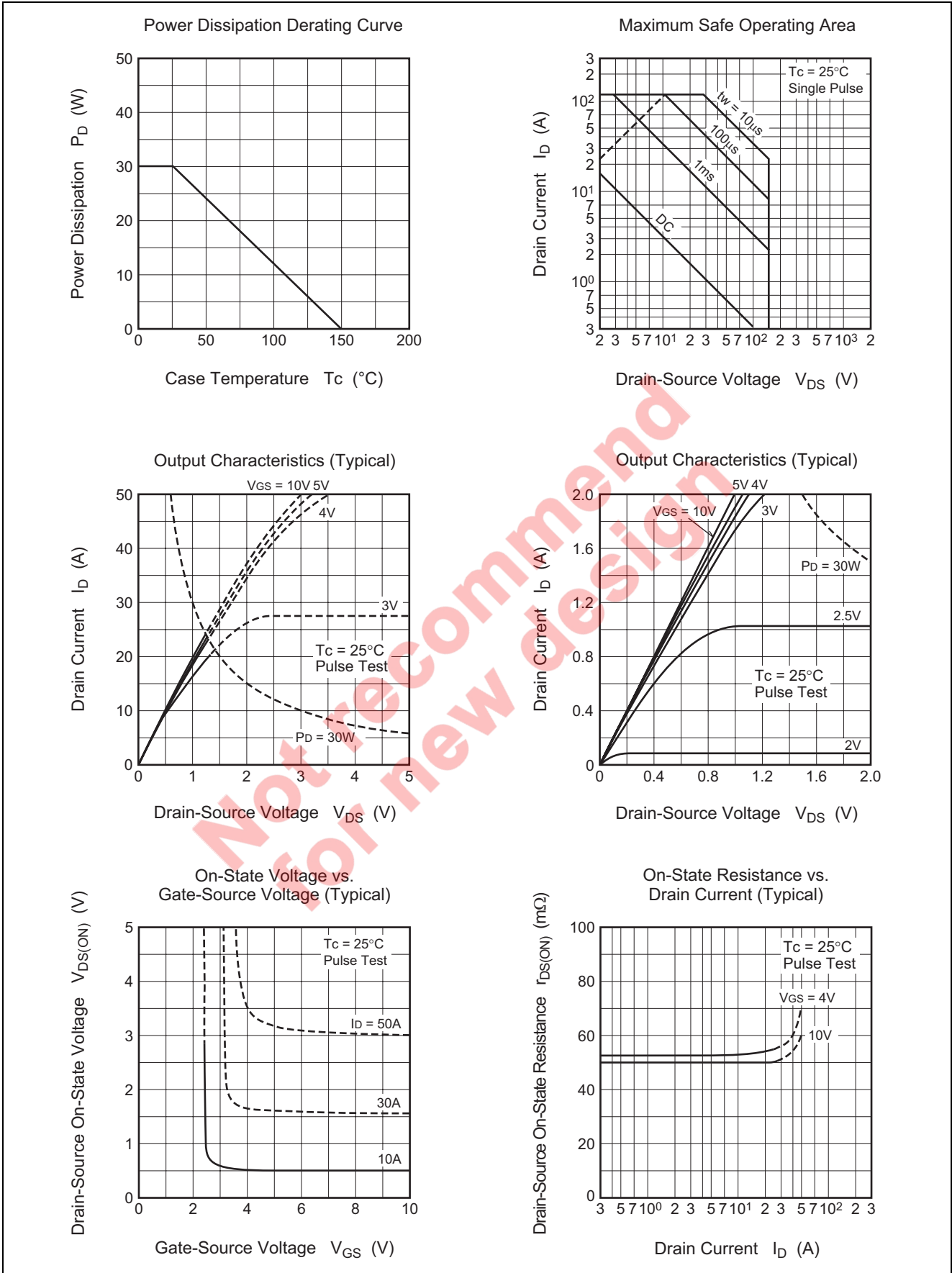
Electrical Characteristics

(T_{ch} = 25°C)

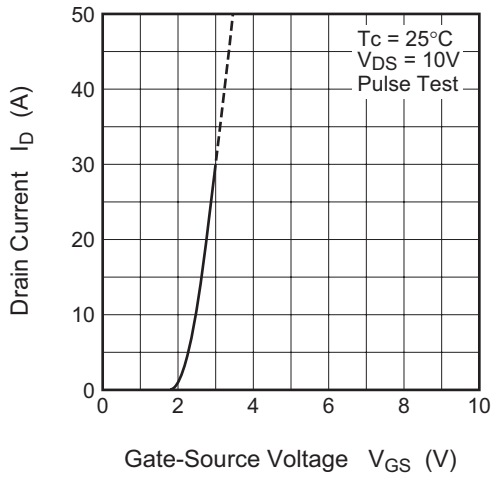
Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain-source breakdown voltage	$V_{(BR)DSS}$	150	—	—	V	$I_D = 1 \text{ mA}$, $V_{GS} = 0 \text{ V}$
Gate-source leakage current	I_{GSS}	—	—	±0.1	μA	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$
Drain-source leakage current	I_{DSS}	—	—	0.1	mA	$V_{DS} = 150 \text{ V}$, $V_{GS} = 0 \text{ V}$
Gate-source threshold voltage	$V_{GS(th)}$	1.0	1.5	2.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Drain-source on-state resistance	$r_{DS(ON)}$	—	66	86	mΩ	$I_D = 15 \text{ A}$, $V_{GS} = 10 \text{ V}$
Drain-source on-state resistance	$r_{DS(ON)}$	—	69	90	mΩ	$I_D = 15 \text{ A}$, $V_{GS} = 4 \text{ V}$
Drain-source on-state voltage	$V_{DS(ON)}$	—	0.99	1.29	V	$I_D = 15 \text{ A}$, $V_{GS} = 10 \text{ V}$
Forward transfer admittance	$ y_{fs} $	—	38	—	S	$I_D = 15 \text{ A}$, $V_{DS} = 10 \text{ V}$
Input capacitance	C_{iss}	—	3000	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	320	—	pF	
Reverse transfer capacitance	C_{rss}	—	160	—	pF	
Turn-on delay time	$t_{d(on)}$	—	22	—	ns	$V_{DD} = 80 \text{ V}$, $I_D = 15 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_{GEN} = R_{GS} = 50 \Omega$
Rise time	t_r	—	42	—	ns	
Turn-off delay time	$t_{d(off)}$	—	280	—	ns	
Fall time	t_f	—	130	—	ns	
Source-drain voltage	V_{SD}	—	1.0	1.5	V	$I_S = 15 \text{ A}$, $V_{GS} = 0 \text{ V}$
Thermal resistance	$R_{th(ch-c)}$	—	—	4.17	°C/W	Channel to case
Reverse recovery time	t_{rr}	—	100	—	ns	$I_S = 30 \text{ A}$, $dI_S/dt = -100 \text{ A}/\mu\text{s}$

Not recommended
for new designs

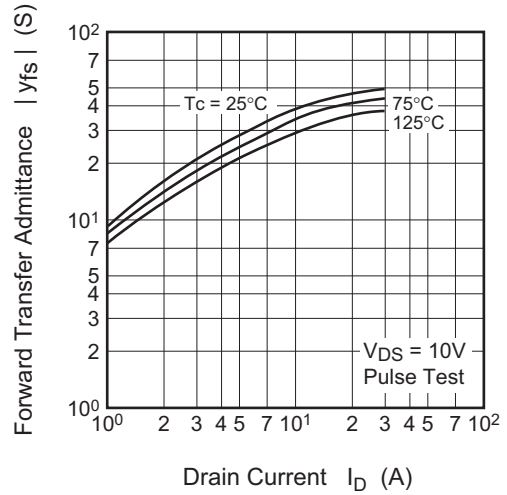
Performance Curves



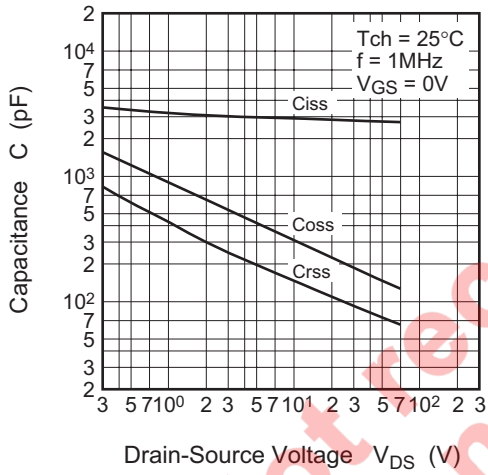
Transfer Characteristics (Typical)



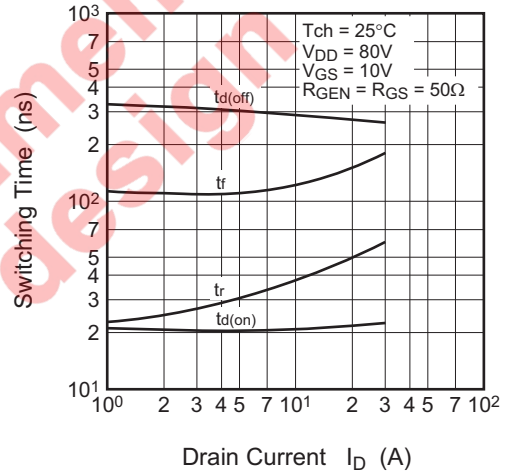
Forward Transfer Admittance vs. Drain Current (Typical)



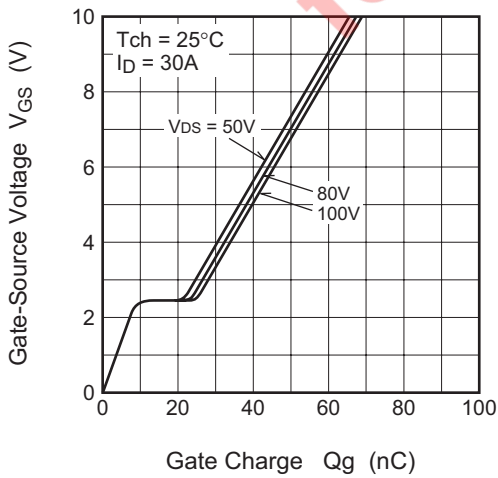
Capacitance vs. Drain-Source Voltage (Typical)



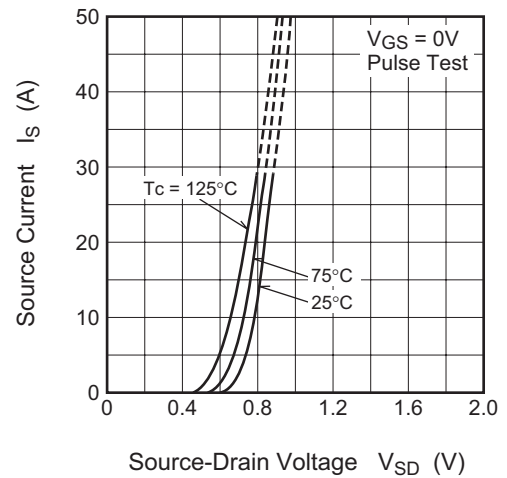
Switching Characteristics (Typical)

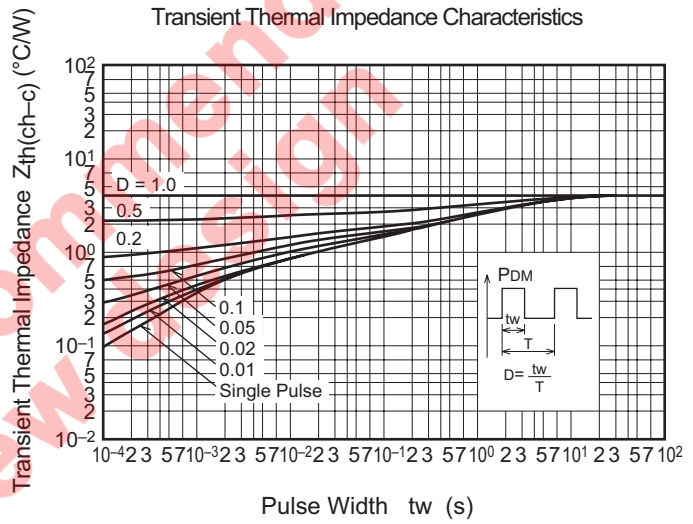
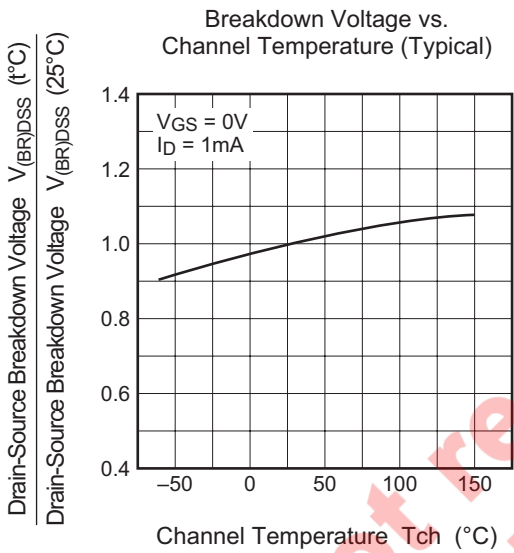
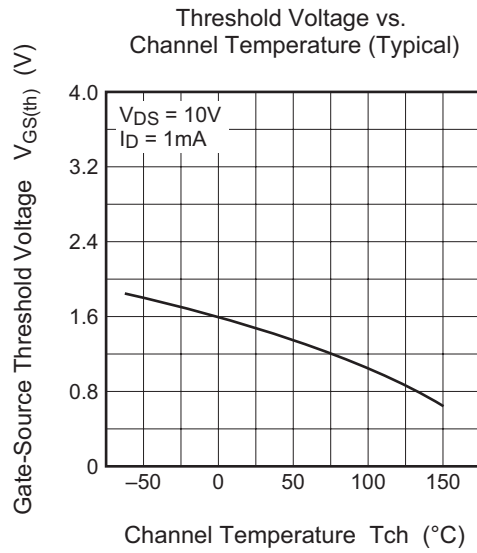
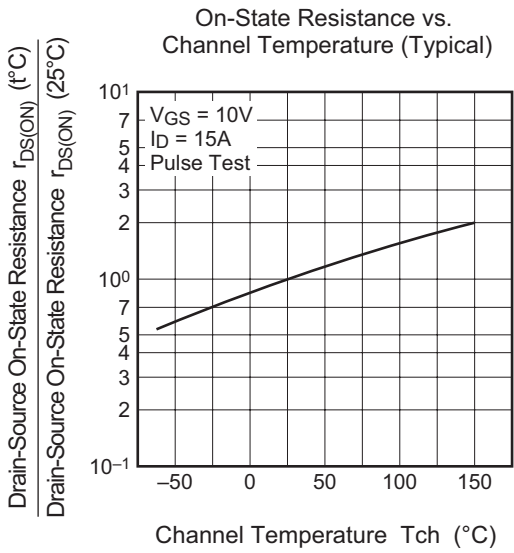


Gate-Source Voltage vs. Gate Charge (Typical)

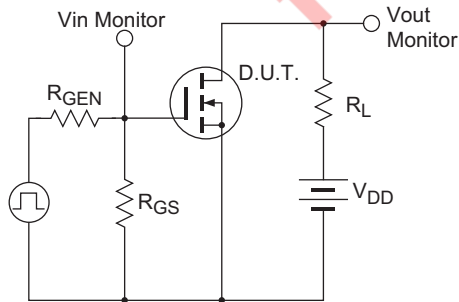


Source-Drain Diode Forward Characteristics (Typical)

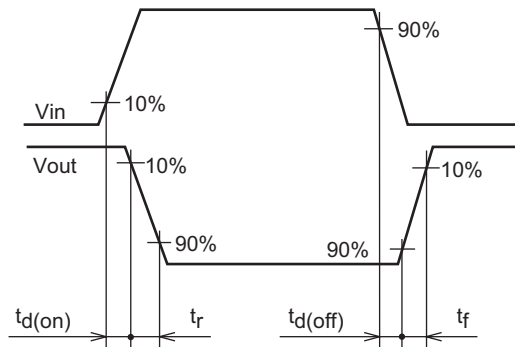




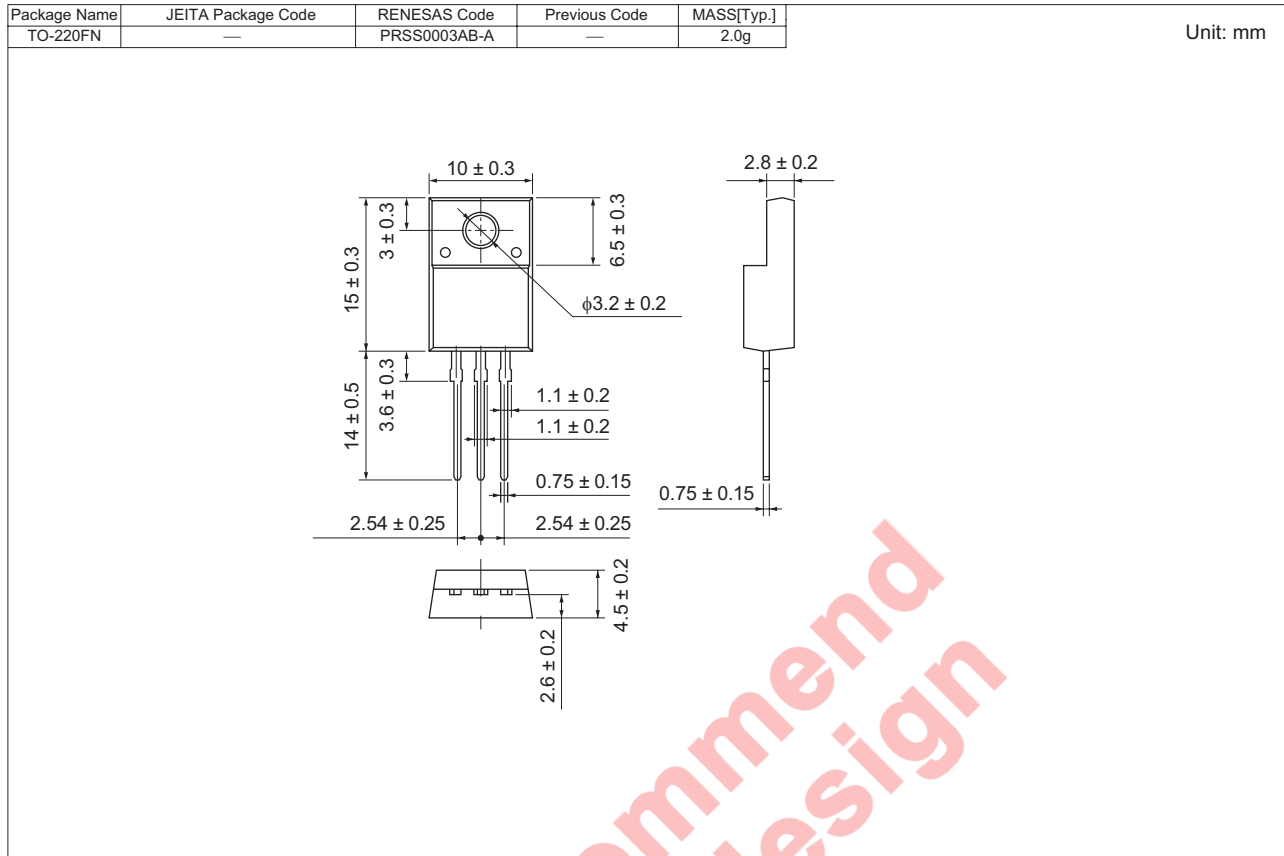
Switching Time Measurement Circuit



Switching Waveform



Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Plastic Magazine (Tube)	50	Type name	FS30KMJ-3
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	FS30KMJ-3-A8

Note : Please confirm the specification about the shipping in detail.

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.

Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120
Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510